DSK Diode Semiconductor Korea **MUR1005F---MUR1060F**

SUPER FAST RECTIFIERS

VOLTAGE RANGE: 50 --- 600 V
CURRENT: 10 A

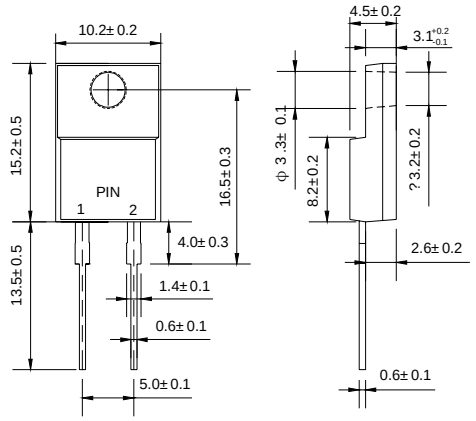
FEATURES

- ◇ Low cost
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with alcohol,Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case:JEDEC ITO-220AC,molded plastic
- ◇ Terminals: Solderable per MIL- STD-750,Method 2026
- ◇ Polarity: As marked
- ◇ Weight: 0.064 ounces,1.81 gram
- ◇ Mounting position: Any

ITO-220AC



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

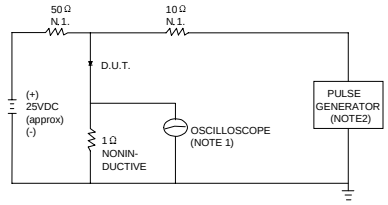
Ratings at 25℃ ambient temperature unless otherwise specified.

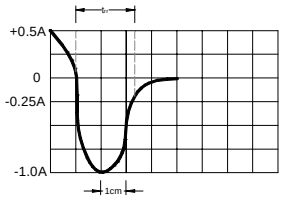
Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		MUR 1005F	MUR 1010F	MUR 1015F	MUR 1020F	MUR 1040F	MUR 1060F	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	150	200	400	600	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	280	420	V
Maximum DC blocking voltage	V_{DC}	50	100	150	200	400	600	V
Maximum average forw ard rectified current @T_C=100℃	$I_{F(AV)}$	10						A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load @T_J=125℃	I_{FSM}	125						A
Maximum instantaneous forw ard voltage @ 10A	V_F	0.975				1.3	1.5	V
Maximum reverse current @T_A=25℃	I_R	5.0				10.0		μA
at rated DC blocking voltage @T_A=125℃		250				500		
Maximum reverse recovery time (Note1)	t_{rr}	25				50		ns
Operating junction temperature range	T_J	- 55 ----- + 150						℃
Storage temperature range	T_{STG}	- 55 ----- + 150						℃

NOTE: 1. Measured with I_F=0.5A, I_R=1A, I_{rr}=0.25A.

FIG.1 – TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC





NOTES:1.RISE TIME = 7ns MAX.INPUT IMPEDANCE =1MΩ. 22pF.
2.RISE TIME =10ns MAX.SOURCE IMPEDANCE=50 Ω.

SET TIME BASE FOR 10/20 ns/cm

FIG.2 -- TYPICAL FORWARD CHARACTERISTIC

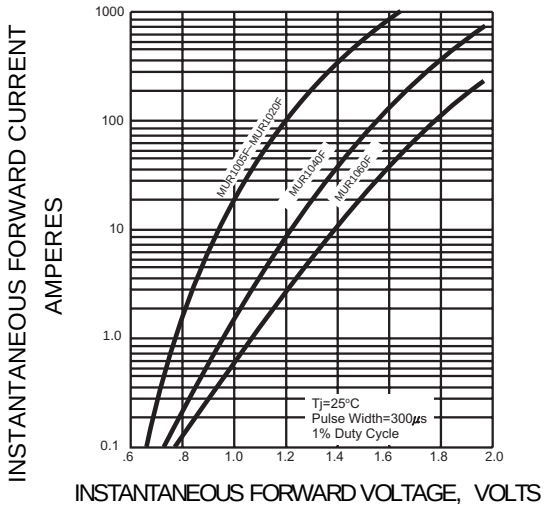


FIG.3 – PEAK FORWARD SURGE CURRENT

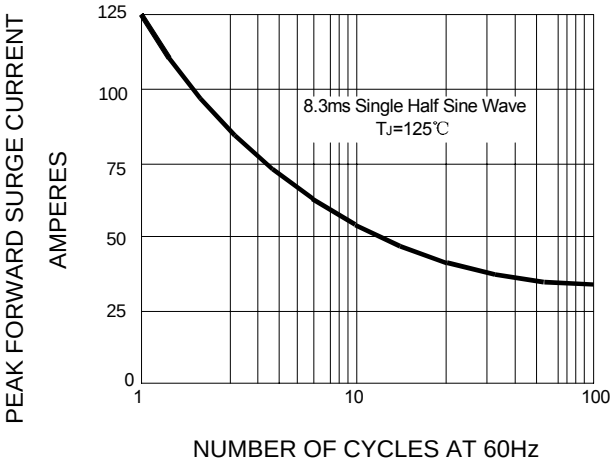


FIG.4-FORWORD DERATING CURVE

